

Features

- High Voltage
- Industrial Standard Package
- Thick Al metal die and double stick bonding
- Thick copper baseplate
- UL E78996 approved
- 3500V_{RMS} isolating voltage

Benefits

- Up to 1600V
- Full compatible TO-240AA
- High Surge capability
- Easy Mounting on heatsink
- Al₂O₃ DBC insulator
- Heatsink grounded

75 A
95 A

Mechanical Description

The Generation V of Add-A-pak module combine the excellent thermal performance obtained by the usage of Direct Bonded Copper substrate with superior mechanical ruggedness, thanks to the insertion of a solid Copper baseplate at the bottom side of the device.

The Cu baseplate allow an easier mounting on the majority of heatsink with increased tolerance of surface roughness and improve thermal spread.

The Generation V of AAP module is manufactured without hard mold, eliminating in this way any possible direct stress on the leads.

The electrical terminals are secured against axial pull-out: they are fixed to the module housing via a click-stop feature already tested and proved as reliable on other IR modules.

Electrical Description

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

Major Ratings and Characteristics

| Parameters | IRKU/V71 | IRKU/V91 | Units |
|--------------------|-------------|----------|--------------------|
| $I_{T(AV)}$ @ 85°C | 75 | 95 | A |
| $I_{T(RMS)}$ | 115 | 150 | A |
| I_{TSM} @ 50Hz | 1665 | 1785 | A |
| @ 60Hz | 1740 | 1870 | A |
| I^2t @ 50Hz | 13.86 | 15.91 | KA ² s |
| @ 60Hz | 12.56 | 14.52 | KA ² s |
| $I^2\sqrt{t}$ | 138.6 | 159.1 | KA ² √s |
| V_{RRM} range | 400 to 1600 | | V |
| T_{STG} | - 40 to 125 | | °C |
| T_J | - 40 to 125 | | °C |



ELECTRICAL SPECIFICATIONS

Voltage Ratings

| Type number | Voltage Code | V_{RRM} , maximum repetitive peak reverse voltage V | V_{RSM} , maximum non-repetitive peak reverse voltage V | V_{DRM} , max. repetitive peak off-state voltage, gate open circuit V | I_{RRM} I_{DRM} 125°C mA |
|--------------|--------------|--|--|--|---------------------------------------|
| IRKU/V71, 91 | 04 | 400 | 500 | 400 | 15 |
| | 08 | 800 | 900 | 800 | |
| | 12 | 1200 | 1300 | 1200 | |
| | 16 | 1600 | 1700 | 1600 | |

On-state Conduction

| Parameters | IRKU/V71 | IRKU/V91 | Units | Conditions | | |
|--|----------|----------|------------------------|---|------------------------------|--|
| $I_{T(AV)}$ Max. average on-state current | 75 | 95 | A | 180° conduction, half sine wave, $T_C = 85^{\circ}\text{C}$ | | |
| $I_{T(RMS)}$ Max. RMS on-state current | 115 | 150 | | DC | | |
| @ T_C | 80 | 75 | °C | | | |
| I_{TSM} Max. peak, one cycle non-repetitive on-state current | 1665 | 1785 | A | $t=10\text{ms}$ | No voltage | Sinusoidal half wave, Initial $T_J = T_J \text{ max.}$ |
| | 1740 | 1870 | | $t=8.3\text{ms}$ | reapplied | |
| | 1400 | 1500 | | $t=10\text{ms}$ | 100% V_{RRM} | |
| | 1470 | 1570 | | $t=8.3\text{ms}$ | reapplied | |
| | 1850 | 2000 | | $t=10\text{ms}$ | $T_J = 25^{\circ}\text{C}$, | |
| | 1940 | 2100 | | $t=8.3\text{ms}$ | no voltage reapplied | |
| I^2t Max. I^2t for fusing | 13.86 | 15.91 | KA^2s | $t=10\text{ms}$ | No voltage | Initial $T_J = T_J \text{ max.}$ |
| | 12.56 | 14.52 | | $t=8.3\text{ms}$ | reapplied | |
| | 9.80 | 11.25 | | $t=10\text{ms}$ | 100% V_{RRM} | |
| | 8.96 | 10.27 | | $t=8.3\text{ms}$ | reapplied | |
| | 17.11 | 20.00 | | $t=10\text{ms}$ | $T_J = 25^{\circ}\text{C}$, | |
| | 15.60 | 18.30 | | $t=8.3\text{ms}$ | no voltage reapplied | |
| $I^2\sqrt{t}$ Max. $I^2\sqrt{t}$ for fusing (1) | 138.6 | 159.1 | KA^2/s | $t=0.1$ to 10ms, no voltage reapplied | | |
| $V_{T(TO)}$ Max. value of threshold voltage (2) | 0.82 | 0.80 | V | Low level (3) | | $T_J = T_J \text{ max}$ |
| | 0.85 | 0.85 | | High level (4) | | |
| r_t Max. value of on-state slope resistance (2) | 3.00 | 2.40 | $\text{m}\Omega$ | Low level (3) | | $T_J = T_J \text{ max}$ |
| | 2.90 | 2.25 | | High level (4) | | |
| V_{TM} Max. peak on-state voltage | 1.59 | 1.58 | V | $I_{TM} = \pi \times I_{T(AV)}$ | | $T_J = 25^{\circ}\text{C}$ |
| | | | | $I_{FM} = \pi \times I_{F(AV)}$ | | |
| di/dt Max. non-repetitive rate of rise of turned on current | 150 | | $\text{A}/\mu\text{s}$ | $T_J = 25^{\circ}\text{C}$, from 0.67 V_{DRM} , $I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500\text{mA}$, $t_r < 0.5 \mu\text{s}$, $t_p > 6 \mu\text{s}$ | | |
| I_H Max. holding current | 200 | | mA | $T_J = 25^{\circ}\text{C}$, anode supply = 6V, resistive load, gate open circuit | | |
| I_L Max. latching current | 400 | | | $T_J = 25^{\circ}\text{C}$, anode supply = 6V, resistive load | | |

(1) I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$.

(3) $16.7\% \times \pi \times I_{AV} < I < \pi \times I_{AV}$

(2) Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

(4) $I > \pi \times I_{AV}$

Triggering

| Parameters | | IRKU/V71 | IRKU/V91 | Units | Conditions | |
|--------------------|---|----------|----------|-------|---|--|
| P _{GM} | Max. peak gate power | 12 | 12 | W | | |
| P _{G(AV)} | Max. average gate power | 3.0 | 3.0 | | | |
| I _{GM} | Max. peak gate current | 3.0 | 3.0 | A | | |
| -V _{GM} | Max. peak negative gate voltage | 10 | | V | T _J = - 40°C T _J = 25°C T _J = 125°C Anode supply = 6V resistive load | |
| V _{GT} | Max. gate voltage required to trigger | 4.0 | | | | |
| | | 2.5 | | | | |
| | | 1.7 | | | | |
| I _{GT} | Max. gate current required to trigger | 270 | | mA | T _J = - 40°C T _J = 25°C T _J = 125°C Anode supply = 6V resistive load | |
| | | 150 | | | | |
| | | 80 | | | | |
| V _{GD} | Max. gate voltage that will not trigger | 0.25 | | V | T _J = 125°C, rated V _{DRM} applied | |
| I _{GD} | Max. gate current that will not trigger | 6 | | mA | T _J = 125°C, rated V _{DRM} applied | |

Blocking

| Parameters | IRKU/V71,91 | Units | Conditions |
|--|------------------------------|------------------|--|
| I_{RRM} Max. peak reverse and off-state leakage current at V_{RRM} , V_{DRM} | 15 | mA | $T_J = 125^\circ\text{C}$, gate open circuit |
| V_{INS} RMS isolation voltage | 2500 (1 min) 3500 (1 sec) | V | 50 Hz, circuit to base, all terminals shorted |
| dv/dt Max. critical rate of rise of off-state voltage (5) | 500 | V/ μs | $T_J = 125^\circ\text{C}$, linear to $0.67 V_{DRM}$, gate open circuit |

(5) Available with $dv/dt = 1000\text{V}/\mu\text{s}$, to complete code add S90 i.e. IRKU91/16AS90.

Thermal and Mechanical Specifications

| Parameters | | IRK.71 | IRK.91 | Units | Conditions |
|-------------------|--|-------------|--------|---------|---|
| T _J | Junction operating temperature range | - 40 to 125 | | °C | |
| T _{stg} | Storage temper. range | - 40 to 125 | | | |
| R _{thJC} | Max. internal thermal resistance, junction to case | 0.165 | 0.135 | K/W | Per module, DC operation |
| R _{thCS} | Typical thermal resistance case to heatsink | 0.1 | | | Mounting surface flat, smooth and greased |
| T | Mounting torque ± 10% to heatsink | 5 | | Nm | A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound |
| | busbar | 3 | | | |
| wt | Approximate weight | 110 (4) | | gr (oz) | |
| Case style | | TO-240AA | | JEDEC | |

ΔR Conduction (per Junction)

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

| Devices | Sine half wave conduction | | | | | Rect. wave conduction | | | | | Units |
|----------|---------------------------|------|------|------|------|-----------------------|------|------|------|------|---------------------------|
| | 180° | 120° | 90° | 60° | 30° | 180° | 120° | 90° | 60° | 30° | |
| IRKU/V71 | 0.06 | 0.07 | 0.09 | 0.12 | 0.18 | 0.04 | 0.08 | 0.10 | 0.13 | 0.18 | $^\circ\text{C}/\text{W}$ |
| IRKU/V91 | 0.04 | 0.05 | 0.06 | 0.08 | 0.12 | 0.03 | 0.05 | 0.06 | 0.08 | 0.12 | |

IRKU/V71, 91 Series

Bulletin I27135 rev. F 10/02

International
IR Rectifier

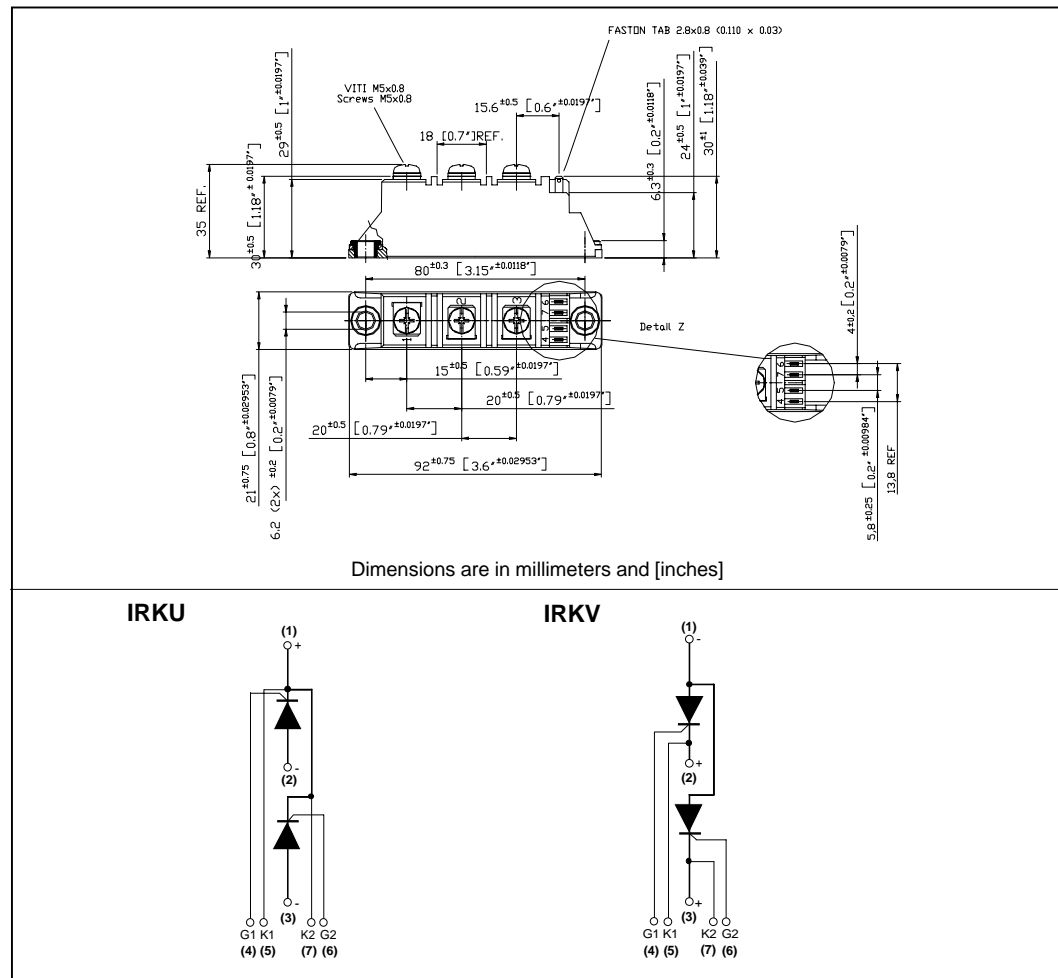
Ordering Information Table

| Device Code | | | | | |
|-------------|----------|---|----------|-----------|--------------|
| 1 | 2 | 3 | 4 | 5 | 6 |
| IRK | U | 91 | / | 16 | A S90 |
| 1 | 2 | 3 | 4 | 5 | 6 |
| 1 | - | Module type | | | |
| 2 | - | Circuit configuration (See Circuit Configuration table) | | | |
| 3 | - | Current code ** | | | |
| 4 | - | Voltage code (See Voltage Ratings table) | | | |
| 5 | - | A : Gen V | | | |
| 6 | - | dv/dt code: S90 = dv/dt 1000 V/μs | | | |
| | | No letter = dv/dt 500 V/μs | | | |

IRK.92 types
With no auxiliary cathode

** Available with no auxiliary cathode.
To specify change: 91 to 92
71 to 72
e.g. : IRKU92/16A etc.

Outline Table



NOTE: To order the Optional Hardware see Bulletin I27900

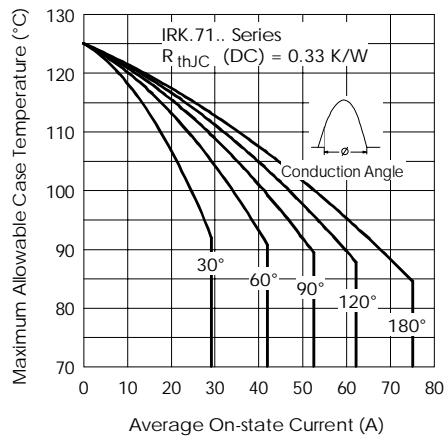


Fig. 1 - Current Ratings Characteristics

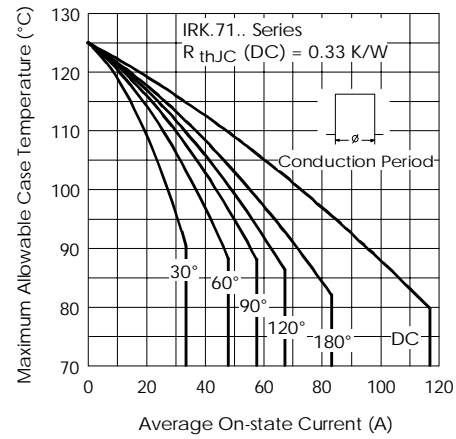


Fig. 2 - Current Ratings Characteristics

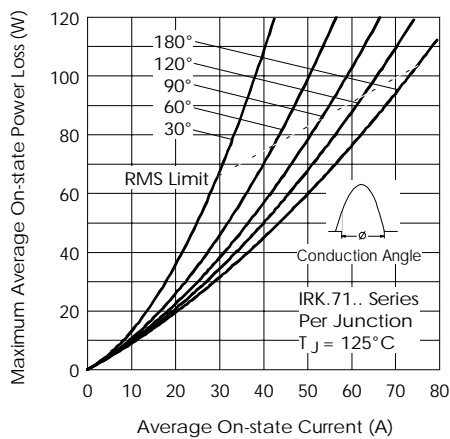


Fig. 3 - On-state Power Loss Characteristics

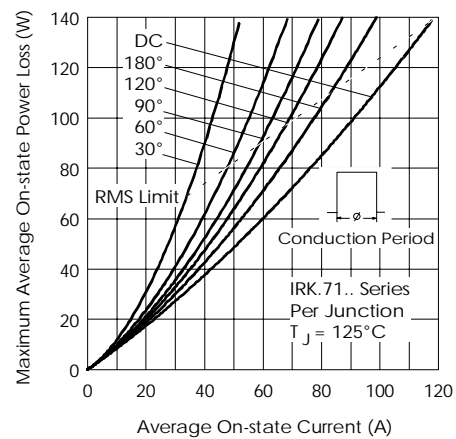


Fig. 4 - On-state Power Loss Characteristics

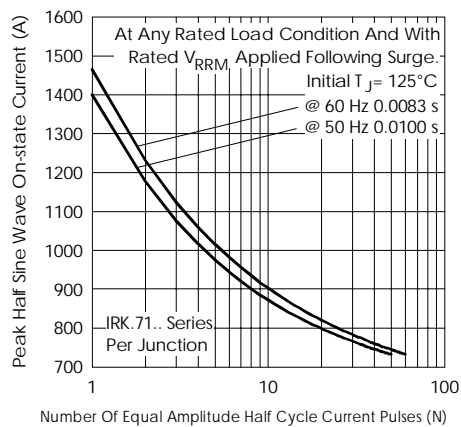


Fig. 5 - Maximum Non-Repetitive Surge Current

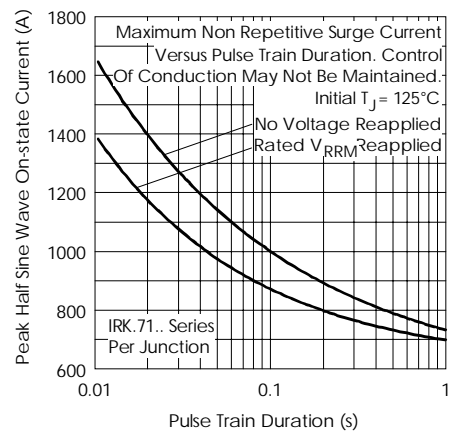


Fig. 6 - Maximum Non-Repetitive Surge Current

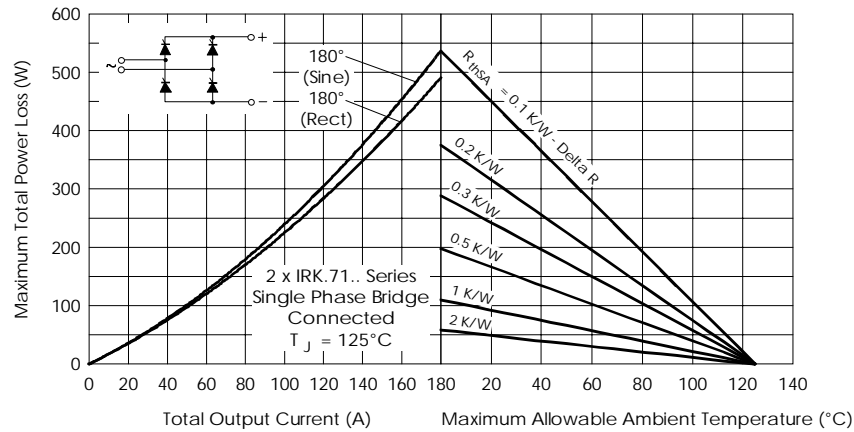


Fig. 7 - On-state Power Loss Characteristics (Single Phase Bridge IRKU+IRKV)

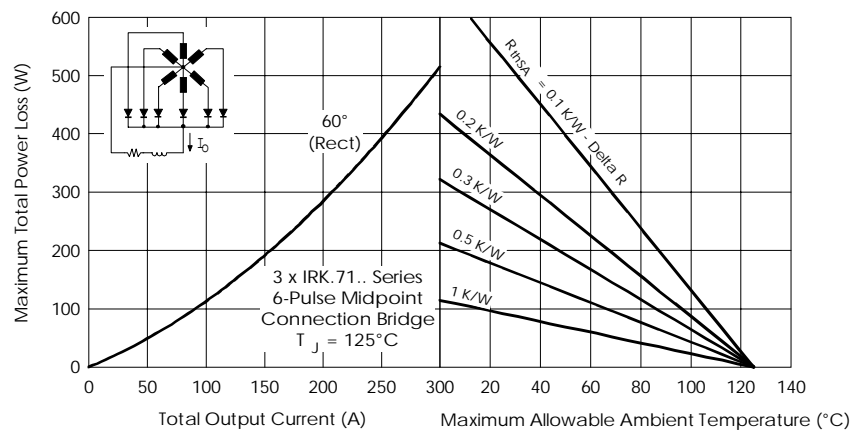


Fig. 8 - On-state Power Loss Characteristics

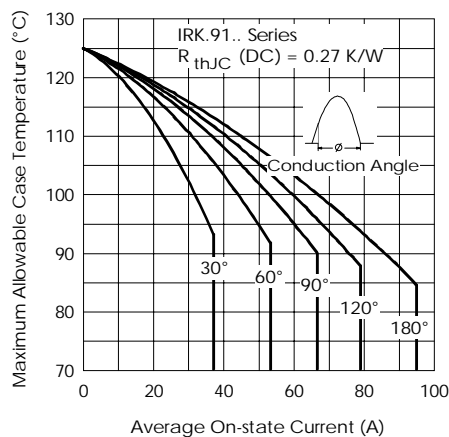


Fig. 9 - Current Ratings Characteristics

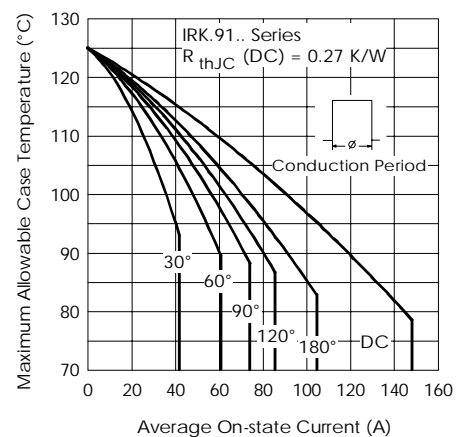


Fig. 10 - Current Ratings Characteristics

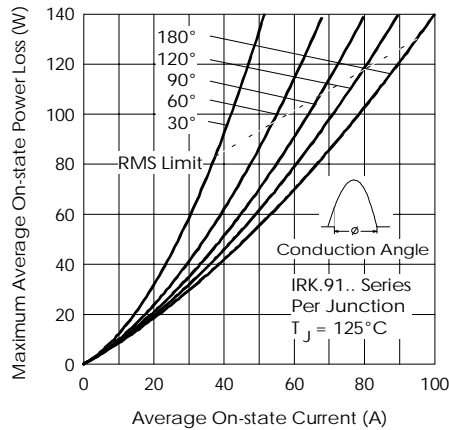


Fig. 11 - On-state Power Loss Characteristics

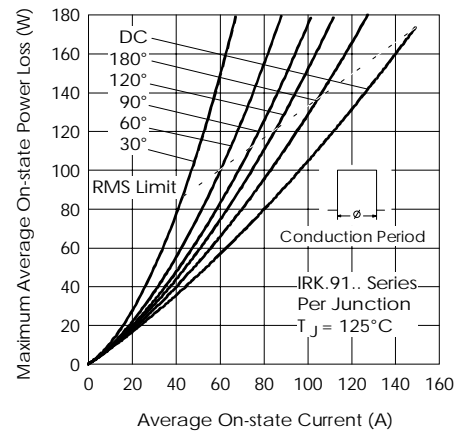


Fig. 12 - On-state Power Loss Characteristics

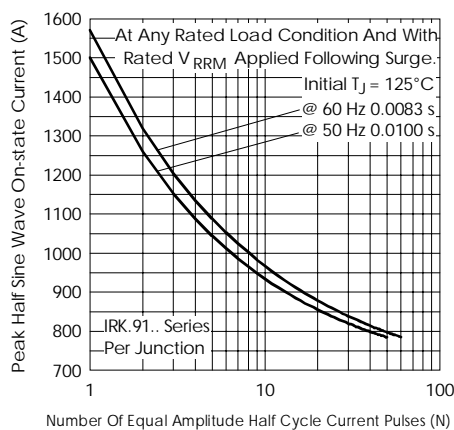


Fig. 13 - Maximum Non-Repetitive Surge Current

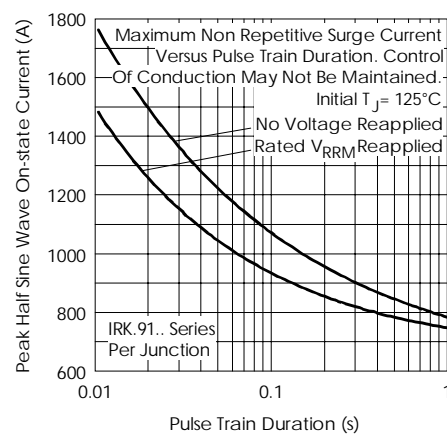


Fig. 14 - Maximum Non-Repetitive Surge Current

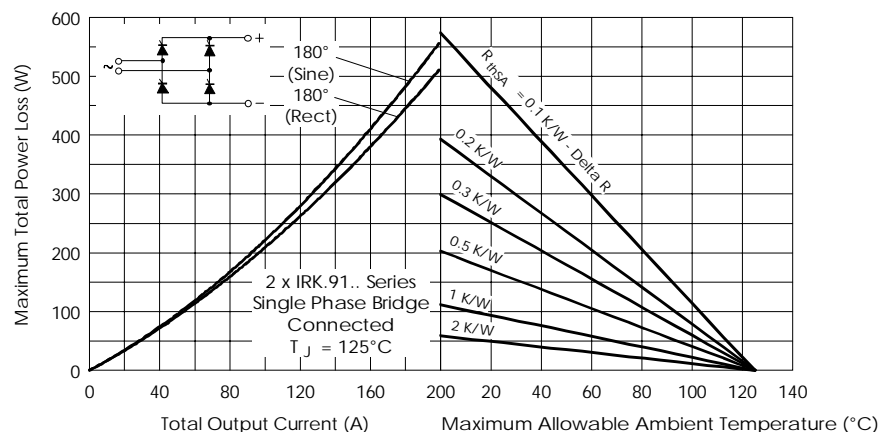


Fig. 15 - On-state Power Loss Characteristics (Single Phase Bridge IRKU+IRKV)

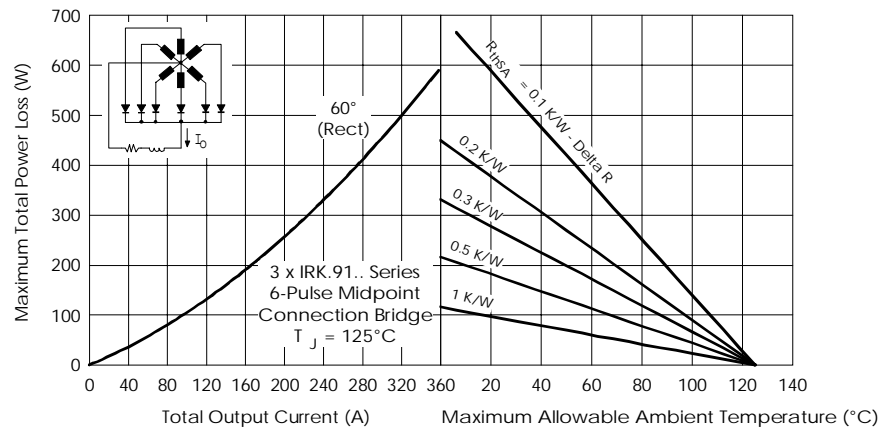


Fig. 16 - On-state Power Loss Characteristics

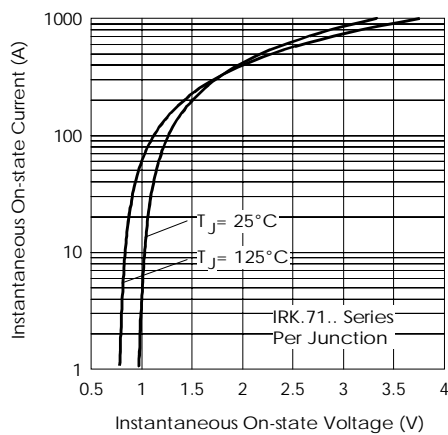


Fig. 17 - On-state Voltage Drop Characteristics

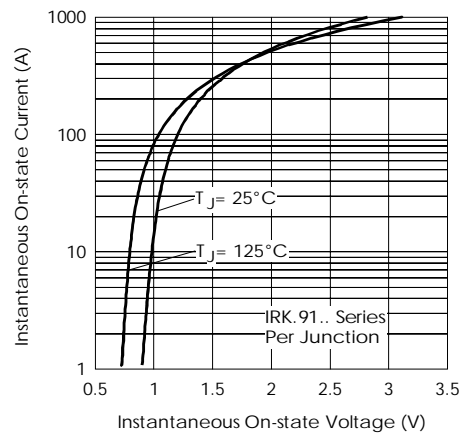


Fig. 18 - On-state Voltage Drop Characteristics

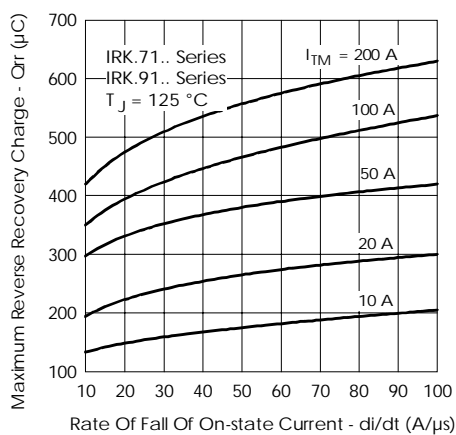


Fig. 19 - Recovery Charge Characteristics

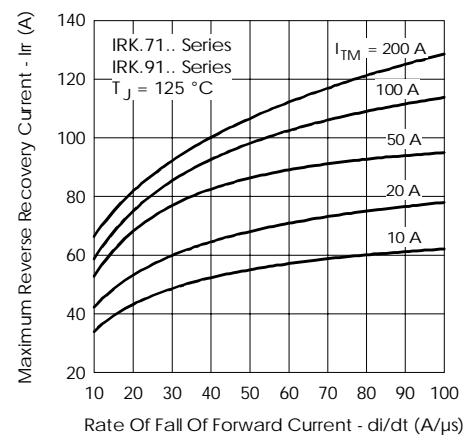


Fig. 20 - Recovery Current Characteristics

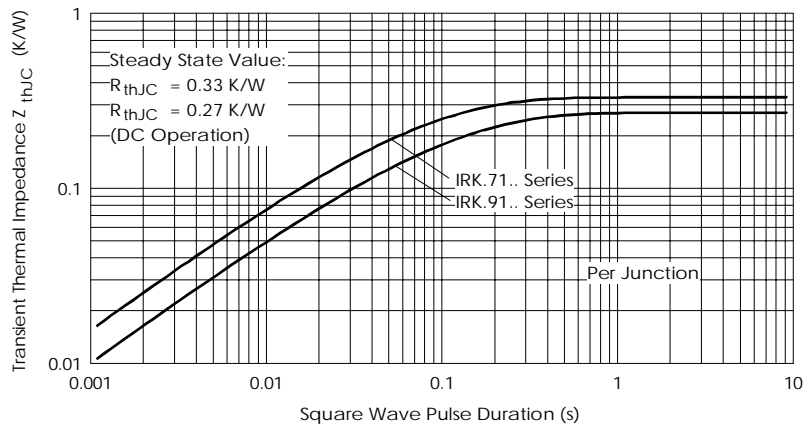


Fig. 21 - Thermal Impedance Z_{thJC} Characteristics

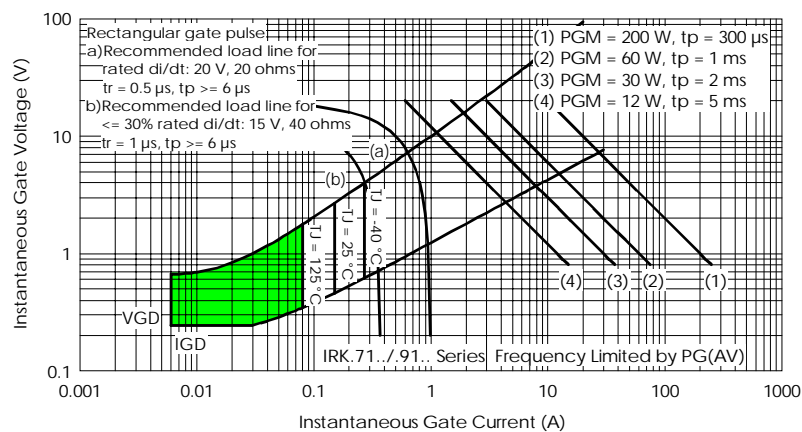


Fig. 22 - Gate Characteristics

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.